

Vishay Siliconix

RoHS

COMPLIANT HALOGEN

FREE

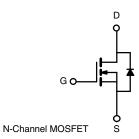
Automotive N-Channel 40 V (D-S) 175 °C MOSFET

| PRODUCT SUMMARY | | | | |
|---|-----------|--|--|--|
| V _{DS} (V) | 40 | | | |
| $R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$ | 0.0017 | | | |
| $R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$ | 0.0020 | | | |
| I _D (A) | 200 | | | |
| Configuration | Single | | | |
| Package | TO-263-7L | | | |



FEATURES

- TrenchFET[®] power MOSFET
- · Package with low thermal resistance
- 100 % R_g and UIS tested
- AEC-Q101 qualified ^d
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



| ABSOLUTE MAXIMUM RATING | GS (T _C = 25 °C, unless | otherwise noted |) | |
|--|---|-----------------------------------|-------------|----|
| PARAMETER | SYMBOL | LIMIT | UNIT | |
| Drain-Source Voltage | | V _{DS} | 40 | V |
| Gate-Source Voltage | | V _{GS} | ± 20 | |
| Continuous Drain Current | T _C = 25 °C a | Ι _D | 200 | |
| | T _C = 125 °C | | 193 | |
| Continuous Source Current (Diode Conduc | tion) ^a | I _S | 200 | А |
| Pulsed Drain Current ^b | | I _{DM} | 600 | |
| Single Pulse Avalanche Current | L = 0.1 mH | I _{AS} | 95 | |
| Single Pulse Avalanche Energy | | E _{AS} | 451 | mJ |
| Mauinum Daura Diasia stian b | T _C = 25 °C | D | 375 | W |
| Maximum Power Dissipation ^b | T _C = 125 °C | P _D | 125 | VV |
| Operating Junction and Storage Temperatu | ure Range | T _J , T _{stg} | -55 to +175 | °C |

| THERMAL RESISTANCE RATINGS | | | | | |
|----------------------------|------------------------|-------------------|-------|------|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Junction-to-Ambient | PCB Mount ^c | R _{thJA} | 40 | °C/W | |
| Junction-to-Case (Drain) | | R _{thJC} | 0.4 | 0/10 | |

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT | |
|---|--------------------------|--|---|------|--------|--------|------|--|
| Static | | 1 | | | | | I | |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} = 0 V, I _D = 250 μA | | 40 | - | - | v | |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = | - V _{GS} , I _D = 250 μΑ | 1.5 | 2.0 | 2.5 | V | |
| Gate-Source Leakage | I _{GSS} | V _{DS} = | 0 V, $V_{GS} = \pm 20$ V | - | - | ± 100 | nA | |
| | | $V_{GS} = 0 V$ | V _{DS} = 40 V | - | - | 1 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{GS} = 0 V$ | $V_{DS} = 40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$ | - | - | 50 | μA | |
| | | $V_{GS} = 0 V$ | $V_{DS} = 40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$ | - | - | 250 | | |
| On-State Drain Current ^a | I _{D(on)} | $V_{GS} = 10 V$ | $V_{DS} \ge 5 V$ | 200 | - | - | Α | |
| | | V _{GS} = 10 V | I _D = 30 A | - | 0.0012 | 0.0017 | | |
| Drain-Source On-State Resistance ^a | Б | $V_{GS} = 10 V$ | I _D = 30 A, T _J = 125 °C | - | - | 0.0028 | | |
| Drain-Source On-State Resistance " | R _{DS(on)} | $V_{GS} = 10 V$ | I _D = 30 A, T _J = 175 °C | - | - | 0.0034 | Ω | |
| | | $V_{GS} = 4.5 V$ | I _D = 20 A | - | 0.0014 | 0.0020 | | |
| Forward Transconductance b | g fs | V _{DS} = 15 V, I _D = 30 A | | - | 181 | - | S | |
| Dynamic ^b | | | | | | | | |
| Input Capacitance | C _{iss} | | | - | 8934 | 11 168 | pF | |
| Output Capacitance | Coss | $V_{GS} = 0 V$ | V _{DS} = 20 V, f = 1 MHz | - | 1592 | 1990 | | |
| Reverse Transfer Capacitance | C _{rss} | | | - | 928 | 1160 | | |
| Total Gate Charge ^c | Qg | | | - | 194 | 291 | | |
| Gate-Source Charge ^c | Q _{gs} | $V_{GS} = 10 V$ | $V_{DS} = 20 \text{ V}, I_D = 20 \text{ A}$ | - | 25 | - | nC | |
| Gate-Drain Charge ^c | Q _{gd} | | | - | 40 | - | 1 | |
| Gate Resistance | Rg | f = 1 MHz | | 0.25 | 0.8 | 1.8 | Ω | |
| Turn-On Delay Time ^c | t _{d(on)} | $V_{DD} = 20 \text{ V}, \text{ R}_L = 1 \Omega$ $\text{I}_D \cong 20 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_g = 1 \Omega$ | | - | 22 | 33 | | |
| Rise Time ^c | t _r | | | - | 17 | 26 | - ns | |
| Turn-Off Delay Time ^c | t _{d(off)} | | | - | 70 | 105 | | |
| Fall Time ^c | t _f | | | - | 16 | 24 | | |
| Source-Drain Diode Ratings and Chara | acteristics ^b | | | | | | | |
| Pulsed Current ^a | I _{SM} | | | - | - | 600 | Α | |
| Forward Voltage | V _{SD} | $I_{\rm F} = 60 \text{ A}, V_{\rm GS} = 0 \text{ V}$ | | - | 0.8 | 1.5 | V | |

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

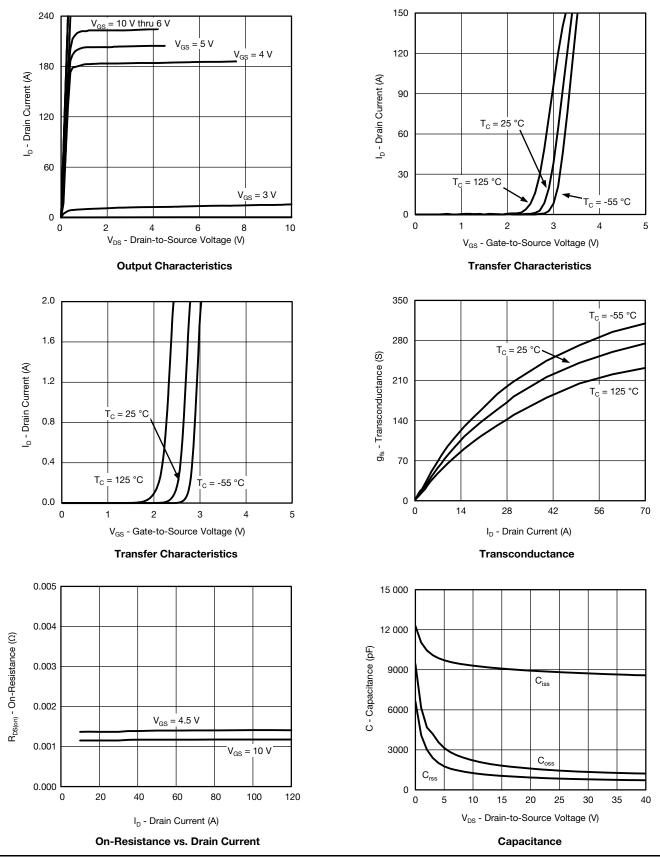
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



S15-1874-Rev. B, 10-Aug-15

Document Number: 67058

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-50

-25 0

S15-1874-Rev. B, 10-Aug-15

25 50

0.5

0.1

-0.3

-0.7

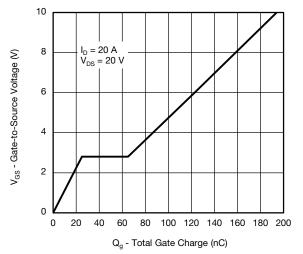
-1.1

-1.5

V_{GS(th)} Variance (V)

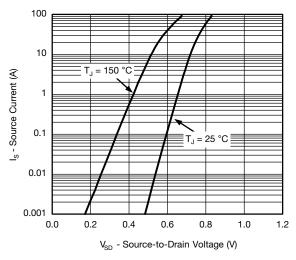
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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



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Gate Charge



Source Drain Diode Forward Voltage

I_D = 250 μA

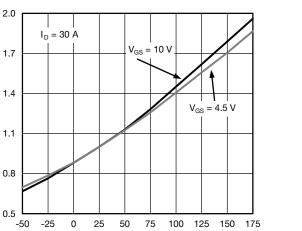
75

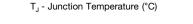
T_J - Temperature (°C) **Threshold Voltage**

100

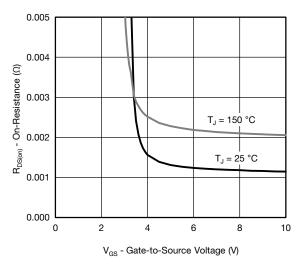
= 5 mA

125 150 175

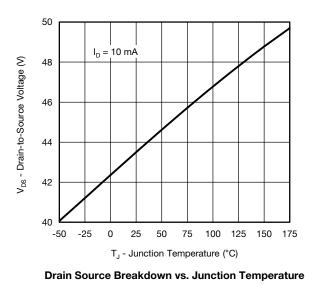




On-Resistance vs. Junction Temperature









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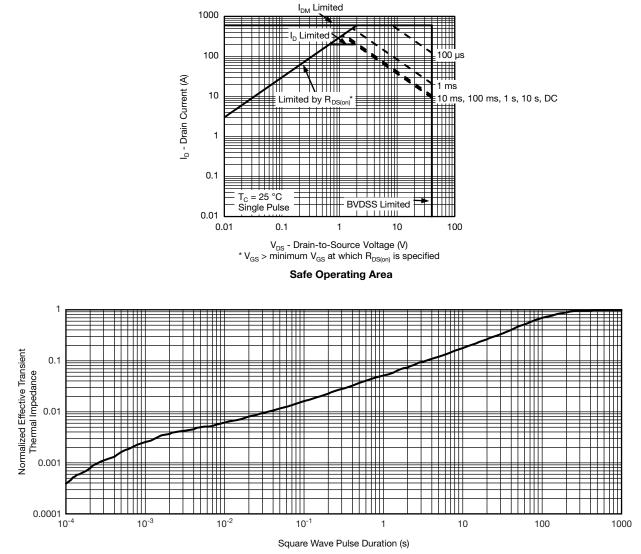
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R_{DS(on)} - On-Resistance (Normalized)



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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)

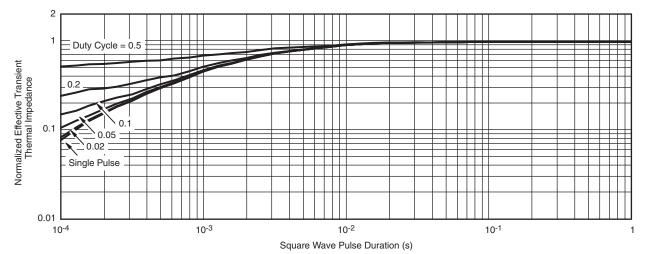


Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67058.



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| REVISION | HISTORY ^a | |
|----------|----------------------|--------------------------------------|
| REVISION | DATE | DESCRIPTION OF CHANGE |
| В | 04-Aug-15 | Revised R _g minimum limit |

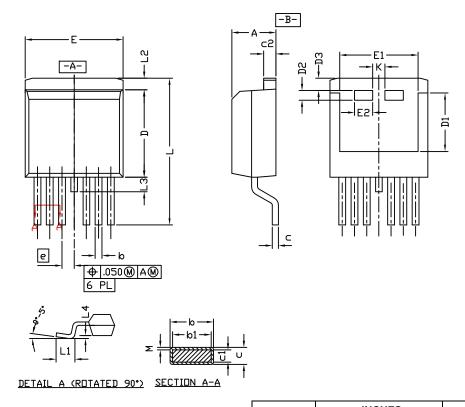
Note

a. As of April 2014



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D²PAK (TO-263-7L) Case Outline



Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin to pin coplanarity max. 4 mils.
- 4. Lead thickness 25 mils.
- 5. For SUM part numbers lead thickness is 24 mils to 29 mils.
- 6. For reference only.
- 7. Use inches as the primary measurement.
- 8. This feature is only for SUM.

| | INCHES | | MILLIMETERS | | |
|--|-----------|-----------|-------------|--------|--|
| DIM. | MIN. | MAX. | MIN. | MAX. | |
| A | 0.160 | 0.190 | 4.064 | 4.826 | |
| b | 0.020 | 0.039 | 0.508 | 0.990 | |
| b1 | 0.020 | 0.035 | 0.508 | 0.889 | |
| b2 | 0.045 | 0.055 | 1.143 | 1.397 | |
| c* SUB | 0.012 | 0.018 | 0.305 | 0.457 | |
| c* SUM | 0.022 | 0.028 | 0.559 | 0.711 | |
| c1 | 0.018 | 0.025 | 0.457 | 0.635 | |
| c2 | 0.045 | 0.055 | 1.143 | 1.397 | |
| D | 0.340 | 0.380 | 8.636 | 9.652 | |
| D1 | 0.220 | 0.240 | 5.588 | 6.096 | |
| D2 | 0.038 | 0.042 | 0.965 | 1.067 | |
| D3 | 0.045 | 0.055 | 1.143 | 1.397 | |
| E | 0.380 | 0.410 | 9.652 | 10.414 | |
| E1 | 0.245 | - | 6.223 | - | |
| E2 | 0.072 | 0.078 | 1.829 | 1.981 | |
| е | 0.050 | 0.050 BSC | | BSC | |
| K | 0.045 | 0.055 | 1.143 | 1.397 | |
| L | 0.575 | 0.625 | 14.605 | 15.875 | |
| L1 | 0.090 | 0.110 | 2.286 | 2.794 | |
| L2 | 0.040 | 0.055 | 1.016 | 1.397 | |
| L3 | 0.050 | 0.070 | 1.270 | 1.778 | |
| L4 | 0.010 BSC | | 0.254 BSC | | |
| М | - | 0.002 | - | 0.050 | |
| ECN: T13-0709-Rev. B, 30-Sep-13 DWG: 6006 | | | | | |

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